

UTC UNISONIC TECHNOLOGIES CO., LTD

BCP68

NPN SILICON TRANSISTOR

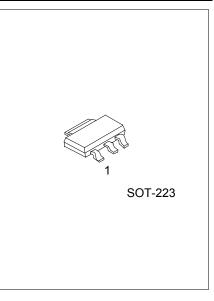
NPN MEDIUM POWER TRANSISTOR

FEATURES

- * High current (max. 1A)
- * Low voltage (max. 20V).
- * Complementary to UTC BCP69

APPLICATIONS

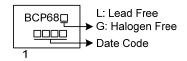
* General purpose switching and amplification under high current conditions.



ORDERING INFORMATION

Ordering Number		Daakaga	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
BCP68L-xx-AA3-R	BCP68G-xx-AA3-R	SOT-223	В	С	Е	Tape Reel	
Note: Pin Assignment: B: B	Note: Pin Assignment: B: Base C: Collector E: Emitter						
BCP68G-xx-AA3-R (1)Packing Type (2)Package Type (3)Rank (4)Green Package		 (1) R: Tape Reel (2) AA3: SOT-223 (3) xx: refer to Classification of hFE3 (4) G: Halogen Free and Lead Free, L: Lead Free 				Lead Free	

MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage (Open Emitter)		V _{CBO}	32	V
Collector-Emitter Voltage (Open Base)		V _{CEO}	20	V
Emitter-Base Voltage (Open Collector)		V _{EBO}	5	V
Collector Current	DC	Ιc	1	А
	Peak	I _{CM}	2	А
Peak Base Current		I _{BM}	200	mA
Total Power Dissipation ($T_A \le 25^{\circ}C$)		PD	1.35	W
Junction Temperature		TJ	+150	°C
Operating Temperature		T _{OPR}	-45 ~ +150	°C
Storage Temperature		T _{STG}	-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction To Ambient	θ _{JA}	91	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified.)

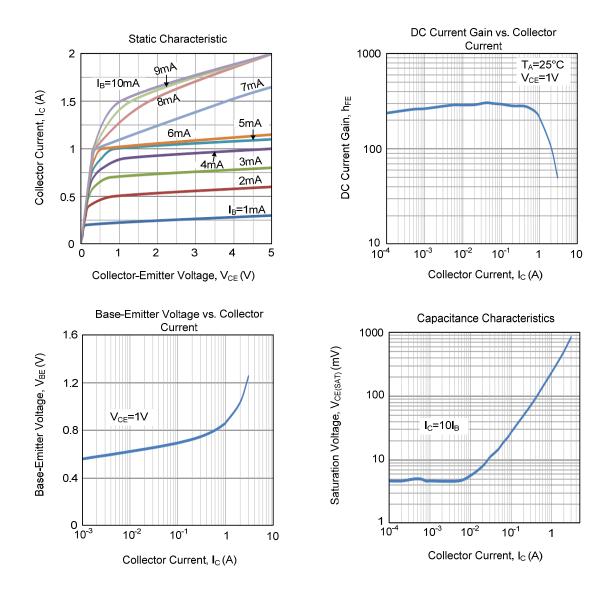
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =1A, I _B =100mA			500	mV
Page Emitter Veltage	V_{BE}	I _C =5mA, V _{CE} =10V		620		mV
Base-Emitter Voltage		I _C =1A, V _{CE} =1V			1	V
Collector Cut-off Current	I _{CBO}	I _E =0, V _{CB} =25V			100	nA
Collector Cut-on Current		I _E =0, V _{CB} =25V,T _J =150°C			10	μA
Emitter Cut-off Current	I _{EBO}	$I_{C}=0, V_{EB}=5V$			100	nA
DC Current Gain	h _{FE}	I _C =500mA, V _{CE} =1V	85		375	
	h _{FE1}	I _C =5mA, V _{CE} =10V	50			
	h _{FE2}	I _C =1A, V _{CE} =1V	60			
	h _{FE3}	$1 - 500 m A \lambda = 1 \lambda$	100		250	
		I _C =500mA, V _{CE} =1V	160		375	
Collector Capacitance	Cc	I _E =i _e =0, V _{CB} =5V, f=1MHz		48		pF
Transition Frequency	f⊤	I _C =-10mA, V _{CE} =-5V, f=100MHz	40			MHz
DC Current Gain Ratio of the Complementary Pairs	h _{FE1} h _{FE2}	I _C =0.5A, V _{CE} =1V			1.6	

CLASSIFICATION OF h_{FE3}

RANK	16	25
RANGE	100~250	160~375



TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

